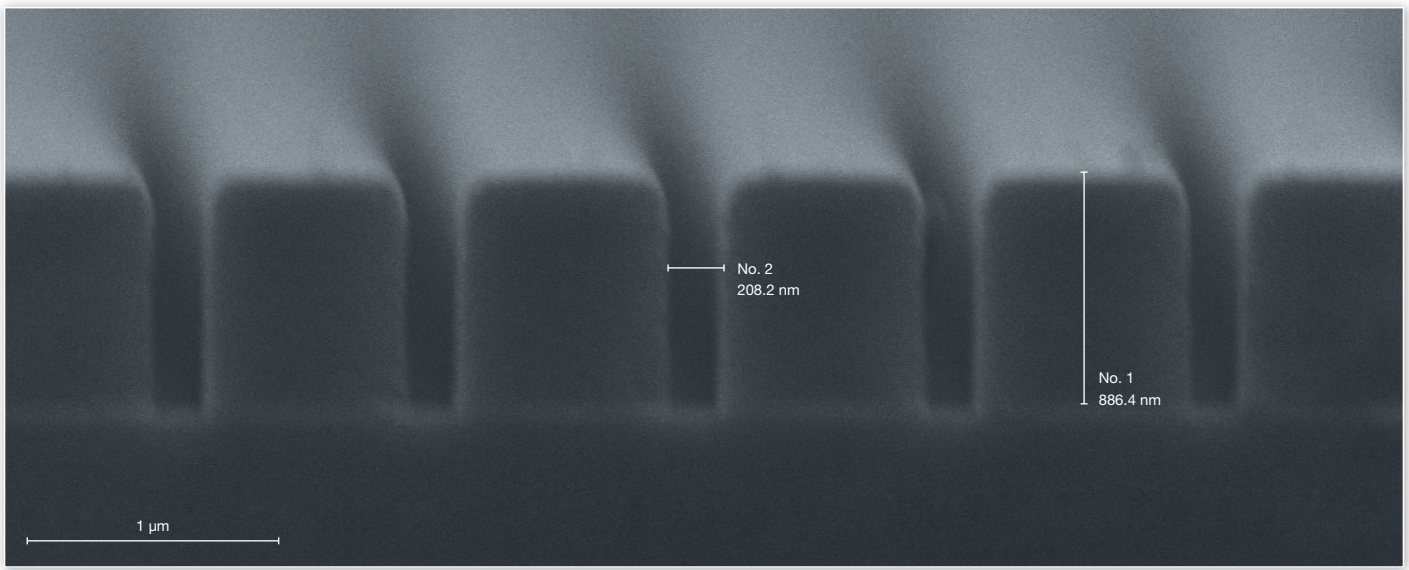
High resolution mode



Measurements performed on SEM

Description

The positive high-contrast resist MiR 701 enables the PICOMASTER to create features well below the specified resolution of 300 nm. In the sample, the lines were exposed with optimized step resolution, to match the address grid of 200 nm. In the design phase, make sure your pattern matches the step size. For example, ensure all features are placed on a 100 nm grid.

References

- AZ MiR 701 14CP
- AZ 326 MIF

Specifications

Materials specifications

Primer	Silane
Photo resist	AZ MiR 701 14CP
Developer	AZ 326 MIF
Substrate	Soda-lime glass

Process specifications

Priming	2000 RPM
Spin coating	4000 RPM
Soft bake	90 sec @ 90°C
Expose	λ = 405 nm Dose: 60 mJ/cm^2
Post bake	None
Developing	60 sec single puddle

PICOMASTER specifications

System	PICOMASTER 100
Scan speed	200 mm/sec
Step size	200 nm
Spot size	0.3 µm

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